To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

MITSUBISHI IGBT

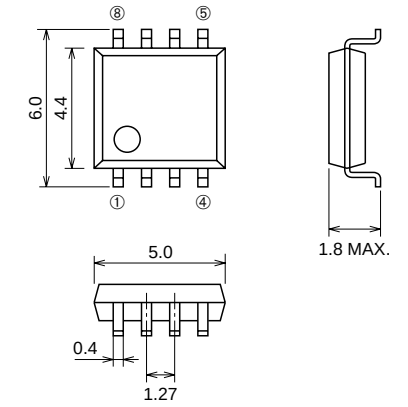
CY25AAJ-8F

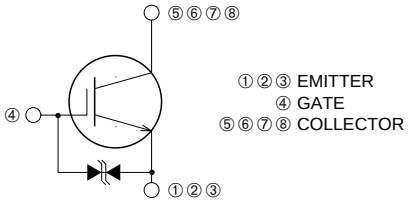
Nch IGBT for STROBE FLASHER

CY25AAJ-8F

- V_{CES} 400V
- I_{CM} 150A
- Drive voltage 4V

OUTLINE DRAWING Dimensions in mm





SOP-8

APPLICATION

Strobe Flasher for camera

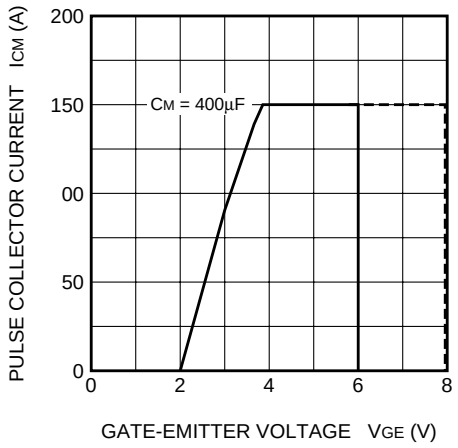
MAXIMUM RATINGS (T_C = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	V_{GE} = 0V	400	V
V_{GES}	Gate-emitter voltage	V_{CE} = 0V	±6	V
V_{GEM}	Peak gate-emitter voltage	V_{CE} = 0V, tw = 10s	±8	V
I_{CM}	Collector current (Pulsed)	C_M = 400µF see figure1	150	A
T_j	Junction temperature		–40 ~ +150	°C
T_{stg}	Storage temperature		–40 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)CES}$	Collector-emitter breakdown voltage	I_C = 1mA, V_{GE} = 0V	450	—	—	V
$V_{(BR)GES}$	Gate-emitter breakdown voltage	I_G = ±100μA, V_{CE} = 0V	±8	—	—	V
I_{CES}	Collector-emitter leakage current	V_{CE} = 400V, V_{GE} = 0V	—	—	10	μA
I_{GES}	Gate-emitter leakage current	V_{GE} = ±6V, V_{CE} = 0V	—	—	±10	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{CE} = 10V, I_C = 1mA	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE